



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hsia, et al.

Serial No.: 09/955,677

Filed: September 19, 2001

For: **Method and Apparatus for High-Resolution In-Situ Plasma Etching of Inorganic and Metal Films**

Art Unit: 2822

Examiner: Soward, Ida

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AMENDMENT AND RESPONSE TO *ADVISORY ACTION*

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Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the *Advisory Action* dated June 3, 2003 in the above-referenced patent application. Please enter and consider the following amendments and remarks in light of the attached *Request for Continued Examination* filed under 37 CFR §1.114 in the above-identified application.